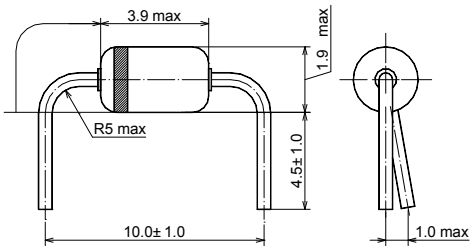
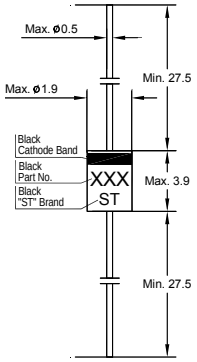
ST60P, ST60S

Silicon Schottky Barrier Diode

Characteristics equivalent to
1N60P and 1N60S



Glass case DO-35-1
Dimensions in mm



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	I_O	50	mA
Peak Forward Current	I_{FM}	150	mA
Surge Forward Current	I_{surge}	500	mA
Junction Temperature	T_j	175	℃
Storage Temperature Range	T_{Stg}	- 55 to + 175	℃

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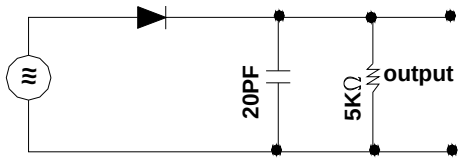
Characteristics at T_a = 25℃

Parameter		Symbol	Min.	Max.	Unit
Forward Current at V_F = 1 V		I_F	4	-	mA
Forward Voltage at I_F = 1 mA at I_F = 5 mA		V_F	- -	0.5 0.7	V
Reverse Current at V_R = 10 V	ST60P ST60S	I_R	- -	50 100	μA
Rectification Efficiency at V_i = 2 Vrms, R = 5 KΩ, C = 20 pF, f = 40 MHz		η	55	-	%



Input 2Vrms

Rectification Efficiency Measurement Circuit

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